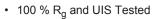
# N-Channel 80 V (D-S) Super Junction Power MOSFET

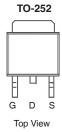
| PRODUCT SUMMARY          |                                   |                                 |                       |  |
|--------------------------|-----------------------------------|---------------------------------|-----------------------|--|
| V <sub>(BR)DSS</sub> (V) | $r_{DS(on)}$ ( $\Omega$ )         | I <sub>D</sub> (A) <sup>c</sup> | Q <sub>g</sub> (Typ.) |  |
| 80                       | 0.0029 at V <sub>GS</sub> = 10 V  | 140                             | 90 nC                 |  |
|                          | 0.0042 at V <sub>GS</sub> = 4.5 V | 90                              | 30110                 |  |

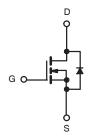
### **FEATURES**











N-Channel MOSFET

| <b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25$                     | °C, unless othe         | rwise noted)                      |                 |    |  |
|--|-------------------------|-----------------------------------|-----------------|----|--|
| Parameter  | Symbol                  | Limit                             | Unit            |    |  |
| Gate-Source Voltage  | V <sub>GS</sub>         | ± 20                              | V               |    |  |
| Continuous Drain Current (T <sub>.I</sub> = 175 °C) <sup>b</sup> | T <sub>C</sub> = 25 °C  | I <sub>D</sub>                    | 140             |    |  |
| Continuous Drain Current (1) = 175 C)                            | T <sub>C</sub> = 100 °C | טי                                | 90 <sup>a</sup> |    |  |
| Pulsed Drain Current   |                         | I <sub>DM</sub>                   | 560             | A  |  |
| Continuous Source Current (Diode Conduction)                     |                         | I <sub>S</sub>                    | 135             |    |  |
| Avalanche Current  |                         | I <sub>AS</sub>                   | 140             |    |  |
| Single Avalanche Energy (Duty Cycle ≤ 1 %) L = 0.1 mH            |                         | E <sub>AS</sub>                   | 300             | mJ |  |
| Maximum Power Dissipation  | T <sub>C</sub> = 25 °C  | Pn                                | 425             | W  |  |
| waxiinani i owei Dissipation                                     | T <sub>C</sub> = 125 °C | , в                               | 150             |    |  |
| Operating Junction and Storage Temperature Range                 |                         | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 175     | °C |  |

| THERMAL RESISTANCE RATINGS               |              |                   |         |         |      |
|--|--------------|-------------------|---------|---------|------|
| Parameter                                |              | Symbol            | Typical | Maximum | Unit |
| Maximum Junction-to-Ambient <sup>a</sup> | t ≤ 10 sec   | R <sub>thJA</sub> | 10      | 15      | °C/W |
| Maximum Junction-to-Ambient              | Steady State |                   | 20      | 35      |      |
| Maximum Junction-to-Case                 |              | $R_{thJC}$        | 0.75    | 1.0     |      |

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c.  $t \le 10 \text{ s.}$



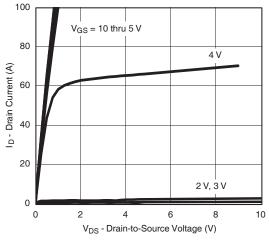


| Parameter                                     | Symbol              | Test Conditions  | Min. | Typ. <sup>a</sup> | Max.    | Unit |  |
|---|---------------------|--|------|-------------------|---------|------|--|
| Static  |                     |  |      | <u>'</u>          | <u></u> |      |  |
| Drain-Source Breakdown Voltage                | V <sub>DS</sub>     | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$                          | 80   |                   |         | v    |  |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$                                   | 1    |                   | 3       |      |  |
| Gate-Body Leakage                             | I <sub>GSS</sub>    | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$                      |      |                   | ± 100   | nA   |  |
|   |                     | V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V                          |      |                   | 1       |      |  |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C |      |                   | 10      | μA   |  |
|   |                     | V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C  |      |                   | 150     |      |  |
| On-State Drain Current <sup>b</sup>           | I <sub>D(on)</sub>  | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V                         | 140  |                   |         | Α    |  |
|   |                     | $V_{GS} = 10 \text{ V}, I_D = 30 \text{A}$                             |      | 0.0029            | 0.0035  |      |  |
|   | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C |      | 0.0034            | 0.0040  |      |  |
| Drain-Source On-State Resistance <sup>b</sup> |                     | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A                         |      | 0.0042            | 0.0055  | Ω    |  |
| Forward Transconductance <sup>b</sup>         | 9 <sub>fs</sub>     | V <sub>DS</sub> = 64 V, I <sub>D</sub> = 30 A                          |      | 85                |         | S    |  |
| Dynamic                                       |                     |  |      | <u>'</u>          |         |      |  |
| Input Capacitance                             | C <sub>iss</sub>    |  |      | 10050             |         |      |  |
| Output Capacitance                            | C <sub>oss</sub>    | $V_{GS} = 0 \text{ V}, V_{DS} = 64 \text{ V}, f = 1 \text{ MHz}$       |      | 3340              |         | pF   |  |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>    |  |      | 460               |         |      |  |
| Total Gate Charge <sup>c</sup>                | Qg                  |  |      | 98                | 120     |      |  |
| Gate-Source Charge <sup>c</sup>               | Q <sub>gs</sub>     | $V_{DS} = 64 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 30 \text{A}$    |      | 20                |         | nC   |  |
| Gate-Drain Charge <sup>c</sup>                | Q <sub>gd</sub>     |  |      | 30                |         |      |  |
| Turn-On Delay Time <sup>c</sup>               | t <sub>d(on)</sub>  |  |      | 10                | 20      |      |  |
| Rise Time <sup>c</sup>                        | t <sub>r</sub>      | $V_{DD}$ = 64 V, $R_L$ = 0.6 $\Omega$                                  |      | 18                | 25      |      |  |
| Turn-Off Delay Time <sup>c</sup>              | t <sub>d(off)</sub> | $I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$     |      | 55                | 80      | ns   |  |
| Fall Time <sup>c</sup>                        | t <sub>f</sub>      |  |      | 15                | 22      |      |  |
| Source-Drain Diode Ratings and Cha            | racteristics (      | T <sub>C</sub> = 25 °C)  |      |                   |         |      |  |
| Pulsed Current                                | I <sub>SM</sub>     |  |      |                   | 560     | Α    |  |
| Diode Forward Voltage                         | V <sub>SD</sub>     | I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V                           |      | 0.8               | 1.5     | V    |  |
| Reverse Recovery Time                         | t <sub>rr</sub>     | I <sub>F</sub> = 30 A, di/dt = 100 A/μs                                |      | 125               | 196     | ns   |  |

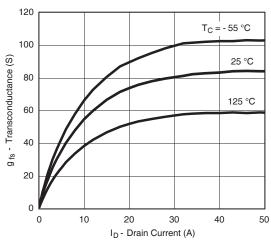
- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

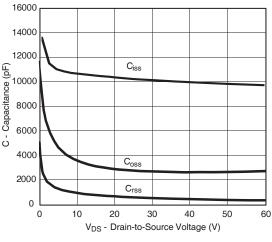
# TYPICAL CHARACTERISTICS (25 °C unless noted)



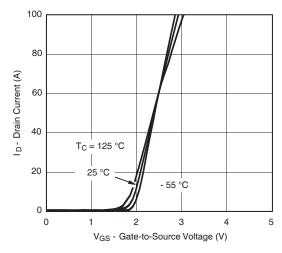
### **Output Characteristics**



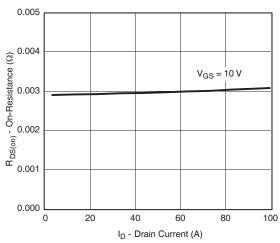
Transconductance



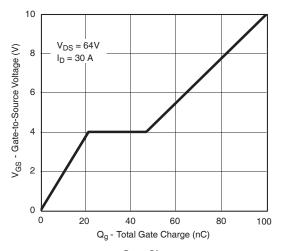
Capacitance



**Transfer Characteristics** 



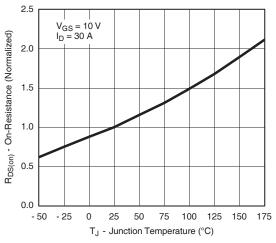
On-Resistance vs. Drain Current



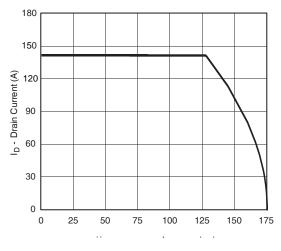
**Gate Charge** 



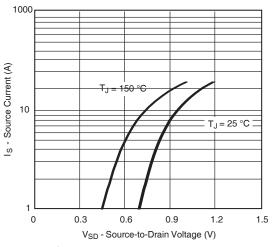
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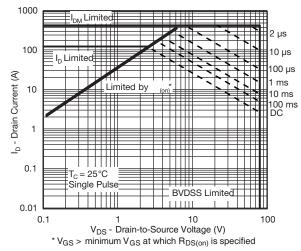
On-Resistance vs. Junction Temperature



Maximum Drain Current vs. Ambient Temperature



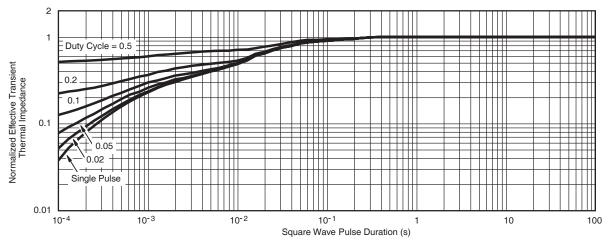
Source-Drain Diode Forward Voltage



Safe Operating Area



## THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case



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